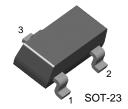


KST5550

High Voltage Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|-------------------------------|-------|-------|
| V_{CBO} | Collector-Base Voltage | 160 | V |
| V _{CEO} | Collector-Emitter Voltage 140 | | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| I _C | Collector Current | 600 | mA |
| P _C | Collector Power Dissipation | 350 | mW |
| T _{STG} | Storage Temperature | 150 | °C |

Electrical Characteristics T_a =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|-----------------------|--------------------------------------|--------------------------------------------------------------------------------------------|----------------|--------------|--------|
| BV _{CBO} | Collector-Base Breakdown Voltage | I _C =10μA, I _E =0 | 160 | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C =1mA, I _B =0 | 140 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | I _E =10μA, I _C =0 | 6 | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} =100V, I _E =0 | | 100 | nA |
| I _{EBO} | Emitter Cut-off Current | V _{EB} =4V, I _C =0 | | 50 | nA |
| h _{FE} | DC Current Gain | V_{CE} =5V, I_{C} =1.0mA V_{CE} =5V, I_{C} =10mA V_{CE} =5V, I_{C} =50mA | 60 60 20 | 250 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I_C =10mA, I_B =1mA I_C =50mA, I_B =5mA | | 0.15 0.25 | V V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I_C =10mA, I_B =1mA I_C =50mA, I_B =5mA | | 1.0 1.2 | V V |
| f _T | Current Gain Bandwidth Product | I _C =10mA, V _{CE} =10V 10 f=100MHz | | 300 | MHz |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=1.0MHz | | 6.0 | pF |



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Typical Characteristics

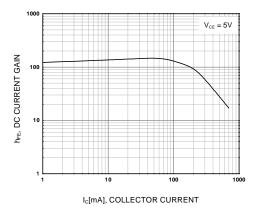


Figure 1. DC current Gain

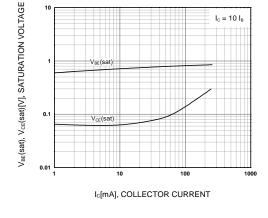


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

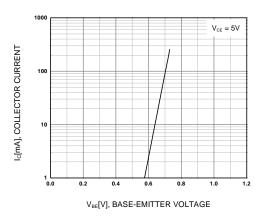


Figure 3. Base-Emitter On Voltage

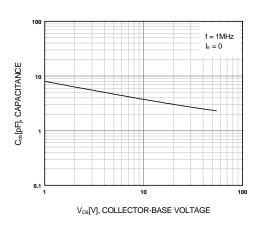


Figure 4. Output Capacitance

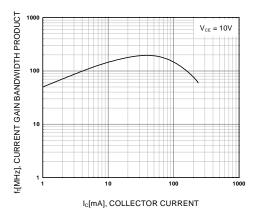
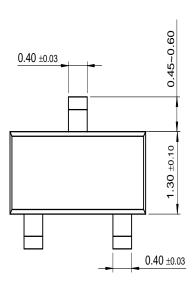
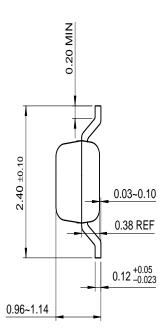


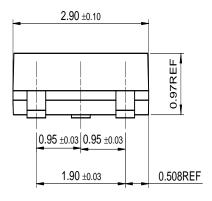
Figure 5. Current Gain Bandwidth Product

Package Dimensions

SOT-23







Dimensions in Millimeters

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